First principles study of d^0 magnetism in SnI_2 monolayer induced by P and As impurities

Pham Minh Tan,[1] Nguyen Thanh Son,[2] Duy Khanh Nguyen,[3,4] J. Guerrero-Sanchez,[5] and D. M. Hoat[6,7,*]

[1]Faculty of Fundamental Sciences, Posts and Telecommunications Institute of Technology, Hanoi, Vietnam

[2]Center of Scientific Research and Application, Lac Hong University, No.10 Huynh Van Nghe Str, Tran Bien Ward, Dong Nai Province, Vietnam

[3]Laboratory for Computational Physics, Institute for Computational Science and Artificial Intelligence, Van Lang University, Ho Chi Minh City, Vietnam

[4]Faculty of Mechanical, Electrical, and Computer Engineering, Van Lang School of Technology, Van Lang University, Ho Chi Minh City, Vietnam

[5]Universidad Nacional Autónoma de México, Centro de Nanociencias y Nanotecnología, Apartado Postal 14, Ensenada, Baja California, Código Postal 22800, Mexico

[6]Institute of Theoretical and Applied Research, Duy Tan University, Ha Noi 100000, Viet Nam

[7]School of Engineering and Technology, Duy Tan University, Da Nang 550000, Viet Nam

*Corresponding author: dominhhoat@duytan.edu.vn

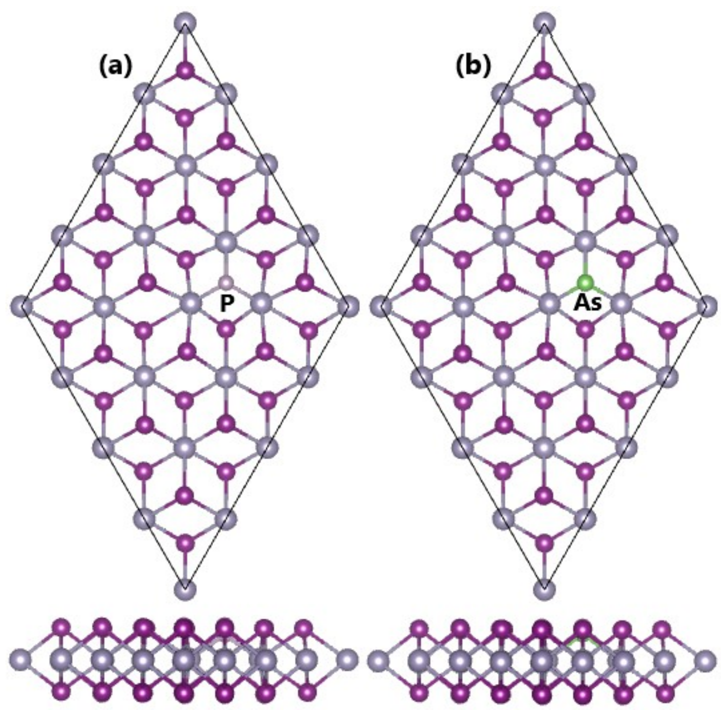

Figure S1: Optimized atomic structure of (a) 1P- and (b) 1As-doped SnI_2 monolayer.

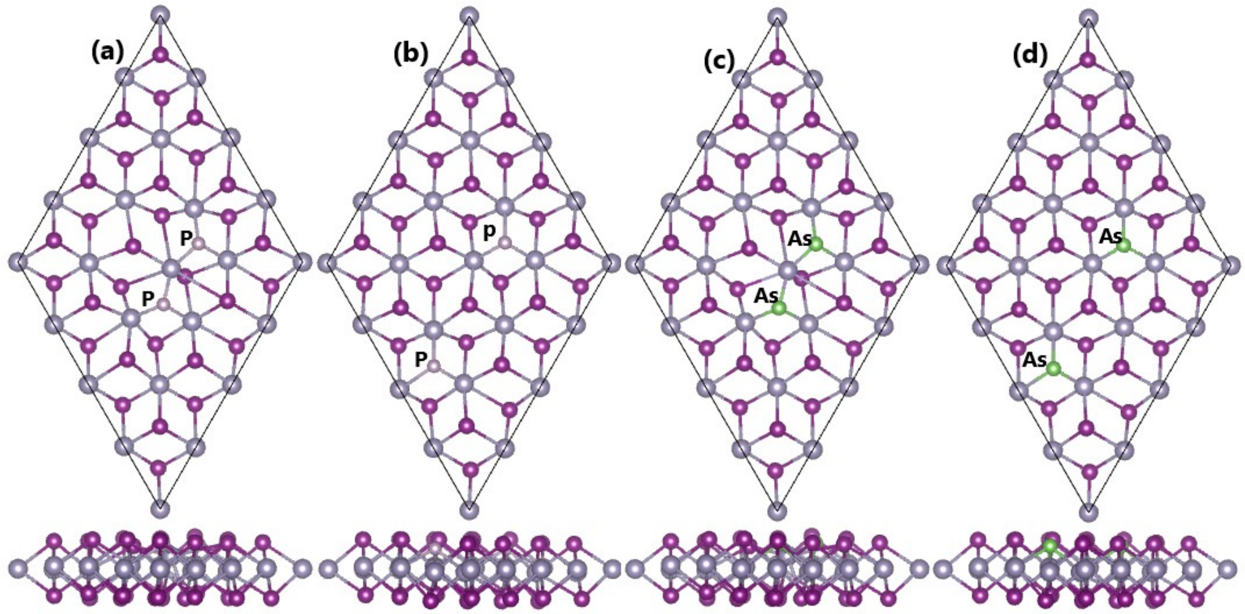

Figure S2: Optimized atomic structure of (a) 2P-1-, (b) 2P-2-, (c) 2As-1-, and (d) 2As-2-doped SnI_2 monolayer.

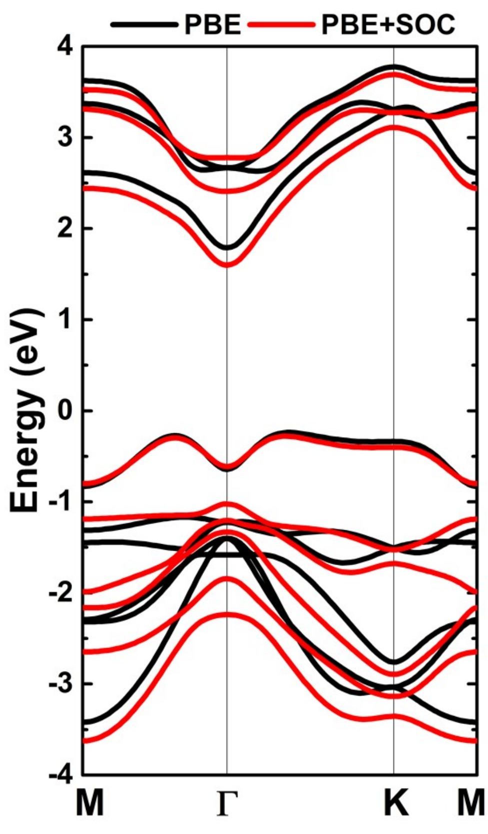

Figure S3: Band structure of SnI_2 monolayer calculated with PBE and PBE+SOC levels (The Fermi level is set to 0 eV).

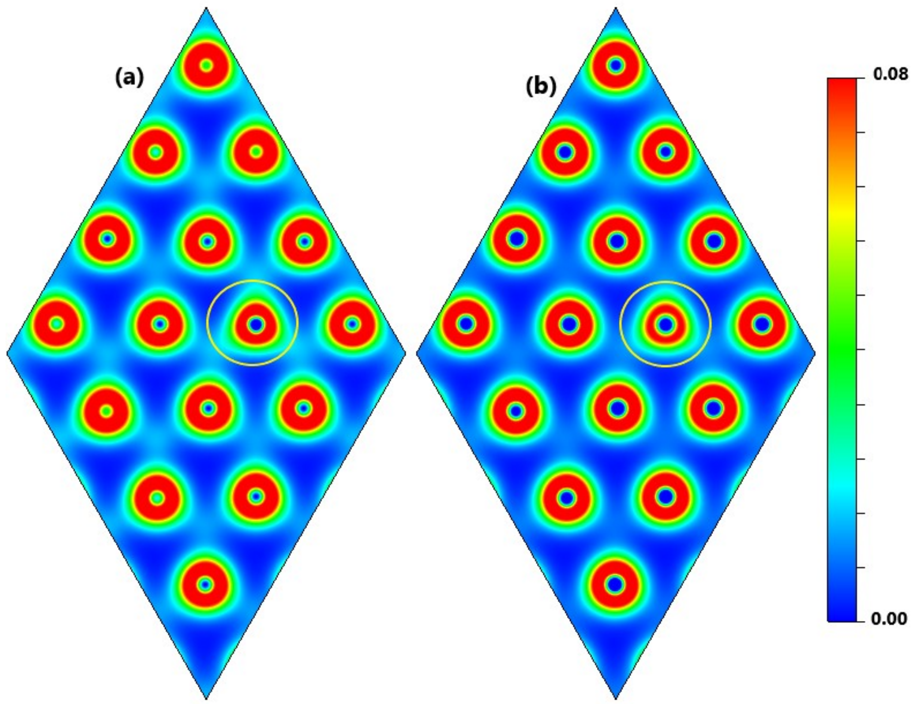

Figure S4: Charge density distributed in (a) 1P- and (b) 1As-doped SnI_2 monolayer (Doping sites are indicated by yellow circles).